

Silicon NPN Power Transistors

2SC1413

DESCRIPTION

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- For TV horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

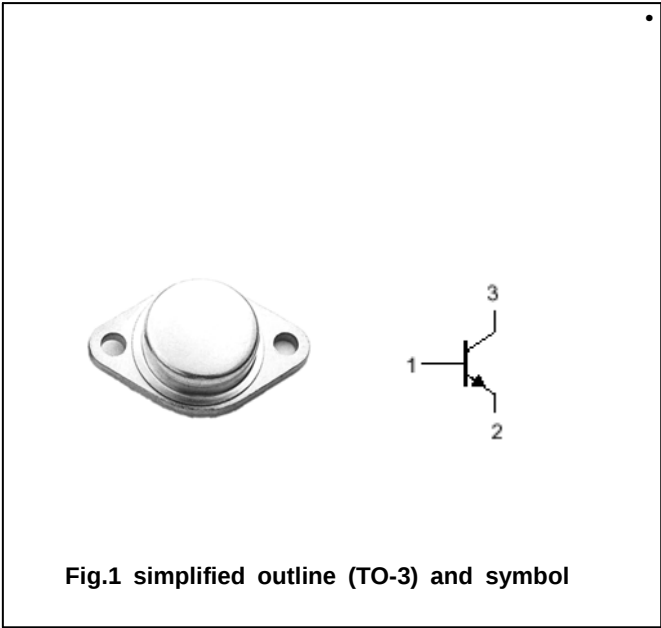


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1200	V
V _{CEO}	Collector-emitter voltage	Open base	500	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		5	A
P _T	Total power dissipation	T _C =25℃	50	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

Silicon NPN Power Transistors**2SC1413****CHARACTERISTICS** $T_j=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.1\text{A}; I_B=0$	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1.0\text{mA}; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5\text{A}; I_B=1.2\text{A}$			10	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5\text{A}; I_B=1.2\text{A}$			2	V
I_{CBO}	Collector cut-off current	$V_{CB}=1200\text{V}; I_E=0$			1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5\text{V}; I_C=0$			1.0	mA
h_{FE}	DC current gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	8			

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PACKAGE OUTLINE

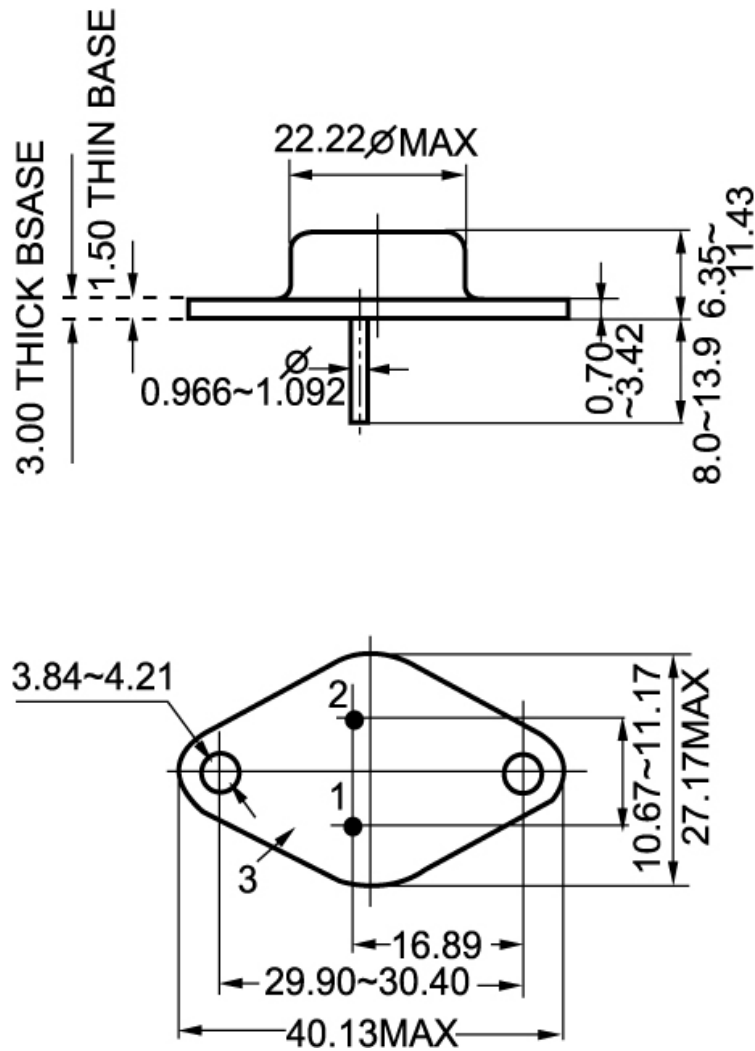


Fig.2 Outline dimensions